

RJP30E2DPP-M0

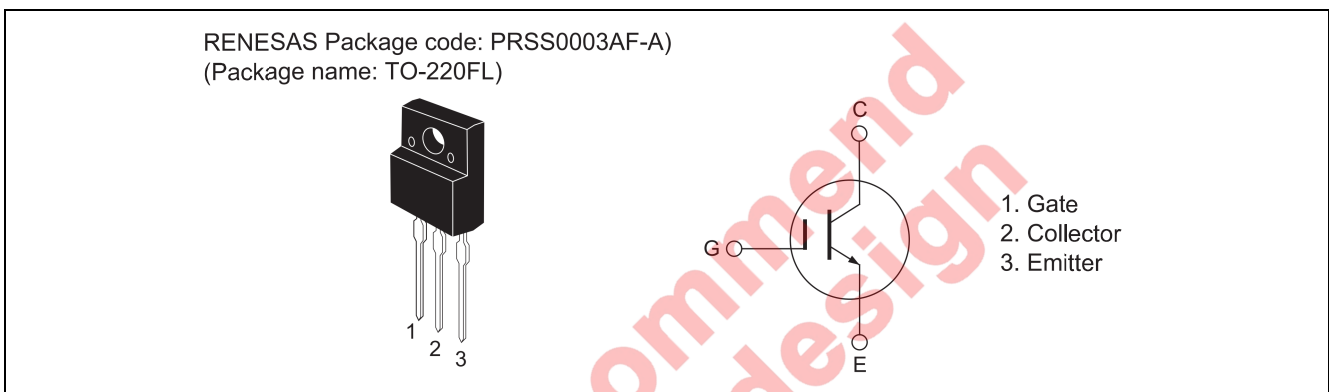
Silicon N Channel IGBT
High Speed Power Switching

R07DS0347EJ0200
Rev.2.00
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Features

- Trench gate technology (G5H series)
- Low collector to emitter saturation voltage $V_{CE(sat)} = 1.7\text{ V typ}$
- High speed switching $t_f = 150\text{ ns typ}$
- Low leak current $I_{CES} = 1\text{ }\mu\text{A max}$
- Isolated package TO-220FL

Outline



Absolute Maximum Ratings

($T_a = 25^\circ\text{C}$)

Item	Symbol	Ratings	Unit
Collector to emitter voltage	V_{CES}	360	V
Gate to emitter voltage	V_{GES}	± 30	V
Collector current	I_c	35	A
Collector peak current	$i_{c(peak)}$ ^{Note1}	200	A
Collector dissipation	P_C ^{Note2}	25	W
Junction to case thermal impedance	θ_{j-c}	5	$^\circ\text{C}/\text{W}$
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Notes: 1. $PW \leq 10\text{ }\mu\text{s}$, duty cycle $\leq 1\%$

2. $T_c = 25^\circ\text{C}$